

**Supporting information: Atomically Abrupt Silicon-Germanium Axial
Heterostructure Nanowires Synthesized in a Solvent Vapor Growth System**

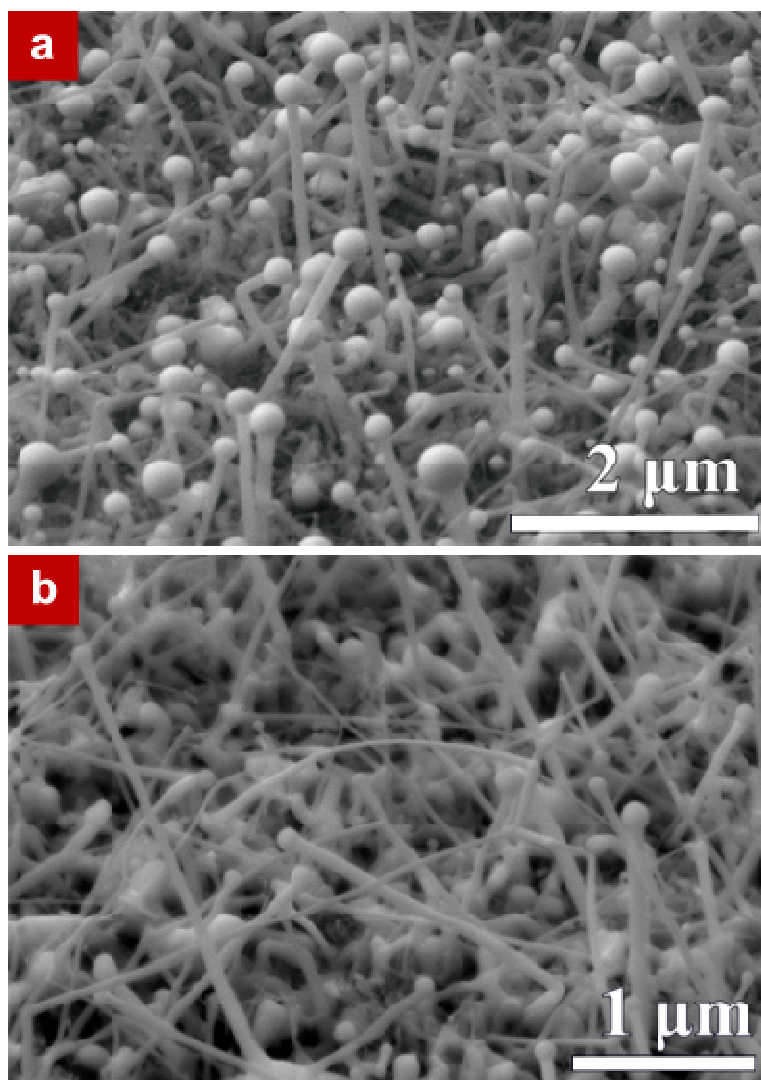


Figure S1: Low magnification SEM image showing seed/NW diameters for a) Sn seeded Si NWs and b) Sn seeded Ge NWs synthesized in the SVG system.

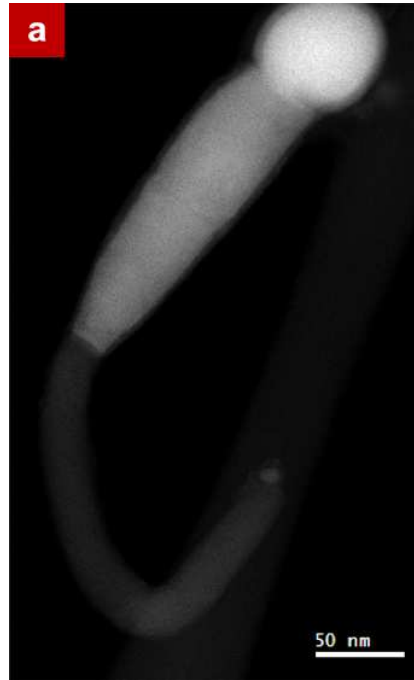


Figure S2: Low magnification HAADF image of Sn catalyzed Ge/Si NW

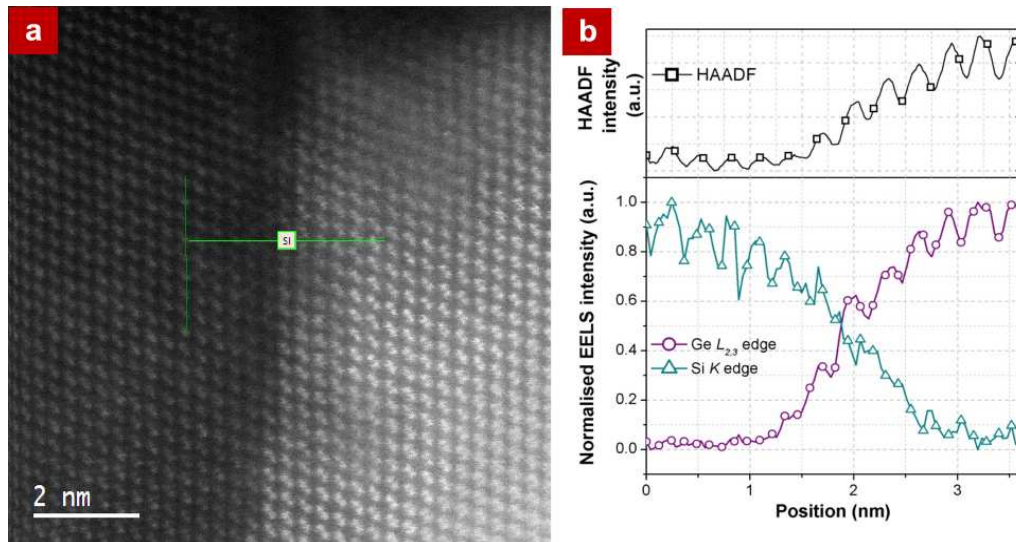


Figure S3: a) HAADF image of the Si/Ge interface at the periphery of the NW presented in Figure 2 of the main paper. The line indicates the direction of the EELS line scan presented in b) which shows a much sharper interfacial abruptness than that noted for the defected middle section of the NW.